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	AB	3	9	3	6	3	2	9	2/1976	Kendall et al.	<del></del>	148	187		-
	AC	3	9	6	2	0	5	2	6/1976	Abbas et al.	204	129.3			
	AD	4	0	4	9	9	0	3	9/1977	Kobler	174	68.5			
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	AN	5	2	7	1	8	0	1	12/1993	Valette		156	653 653 21	, <u>K</u>	
	AO	5	7	4	7	3	5	3	5/5/1998	Bashir et al.		437	21 /	3/1/2	i
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